

# Zhipeng Dong

## List of Publications by Year in descending order

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10  
papers

434  
citations

1307594

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1474206

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all docs

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docs citations

10  
times ranked

946  
citing authors

#	ARTICLE	IF	CITATIONS
1	A Novel Program Suspend Scheme for Improving the Reliability of 3D NAND Flash Memory. IEEE Journal of the Electron Devices Society, 2022, 10, 98-103.	2.1	1
2	On Low-Resistance Contacts to 2-D MoTe <sub>2</sub> by Crystalline Phase Junctions. IEEE Transactions on Electron Devices, 2018, 65, 1583-1588.	3.0	6
3	On Image Charge Induced Barrier Lowering in Graphene-Semiconductor Contacts. IEEE Nanotechnology Magazine, 2018, 17, 320-324.	2.0	0
4	Tunneling current in HfO <sub>2</sub> and Hf <sub>0.5</sub> Zr <sub>0.5</sub> O <sub>2</sub> -based ferroelectric tunnel junction. Journal of Applied Physics, 2018, 123, .	2.5	27
5	Atomically Thin CBRAM Enabled by 2-D Materials: Scaling Behaviors and Performance Limits. IEEE Transactions on Electron Devices, 2018, 65, 4160-4166.	3.0	19
6	Assessment of 2-D Transition Metal Dichalcogenide FETs at Sub-5-nm Gate Length Scale. IEEE Transactions on Electron Devices, 2017, 64, 622-628.	3.0	24
7	A Simple Model of Negative Capacitance FET With Electrostatic Short Channel Effects. IEEE Transactions on Electron Devices, 2017, 64, 2927-2934.	3.0	65
8	Atomically Thin Femtojoule Memristive Device. Advanced Materials, 2017, 29, 1703232.	21.0	147
9	Vertical Organic Field-Effect Transistors for Integrated Optoelectronic Applications. ACS Applied Materials & Interfaces, 2016, 8, 10430-10435.	8.0	61
10	Performance Limits Projection of Black Phosphorous Field-Effect Transistors. IEEE Electron Device Letters, 2014, 35, 963-965.	3.9	84